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Thermal Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
P_D	Power Dissipation	227	mW
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient ⁽³⁾	550	$^\circ\text{C}/\text{W}$

Note:

3. Minimum land pad.

Electrical Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
V_R	Breakdown Voltage	$I_R = 10 \mu\text{A}$	40		V
V_F	Forward Voltage	$I_F = 1 \text{ mA}$		380	mV
		$I_F = 40 \text{ mA}$		1000	mV
I_R	Reverse Leakage	$V_R = 30 \text{ V}$		0.2	μA
t_{rr}	Reverse Recovery Time	$I_F = I_R = 10 \text{ mA}$, $i_{rr} = 0.1I_R$		8.0	nS
C_J	Junction Capacitance	$V_R = 0$, $f = 1.0 \text{ MHz}$		5.0	pF

Typical Performance Characteristics

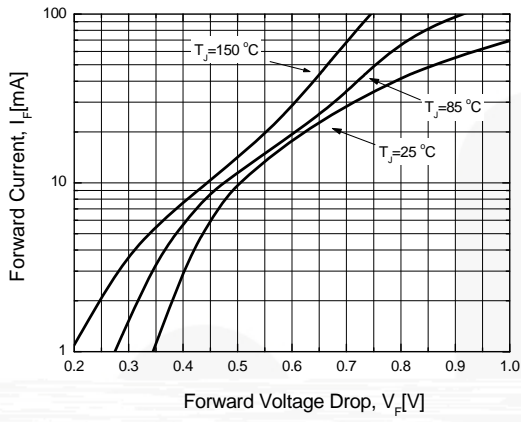


Figure 1. Forward Current Characteristics

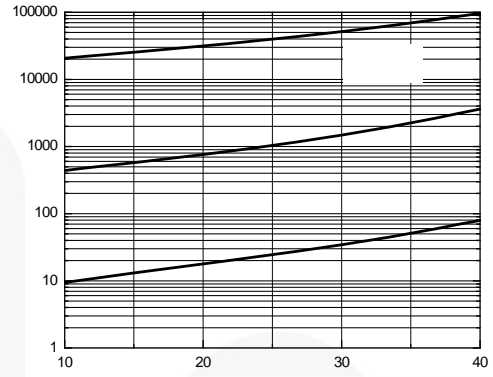


Figure 2. Reverse Leakage Current

Figure 3. Junction Capacitance

Figure 4. Power Derating



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